

		Which type of MOSFET is ideal for switching applications? Give reason			
		OR			
4	a)	With switching models and waveforms, explain the dynamic characteristics of MOSFET	CO3	PO2	10
	b)	The bipolar transistor is specified to have β_F in the range of 8 to 40. The load resistance is $R_C = 11 \Omega$. The dc supply voltage is $V_{CC} = 200 \text{ V}$ and the input voltage to the base circuit is $V_B = 10 \text{ V}$. If $V_{CE(sat)} = 1.0 \text{ V}$ and $V_{BE(sat)} = 1.5 \text{ V}$, find (a) the value of R_B that results in saturation with an ODF of 5, (b) the β_{forced} .	CO3	PO2	10
		UNIT - IV			
5	a)	What are the advantages of SiC IGBTs over normal Si based IGBTs? Justify your answer with structural diagram of SiC IGBT	CO3	PO2	10
	b)	Why is it important to isolate gate and base drive circuits in a power electronic converter? Discuss any two methods of isolation	CO4	PO2	10
		OR			
6	a)	With a neat cross-sectional diagram discuss the working of IGBT. Plot the static characteristics	CO3	PO2	10
	b)	With relevant circuit diagram, explain the working of the following base control techniques of a transistor. (i) Proportional base control (ii) Antisaturation base control	CO4	PO2	10
		UNIT - V			
7	a)	With the circuit diagram and relevant waveforms, discuss the operation of synchronized UJT firing circuit for firing an SCR.	CO3	PO2	10
	b)	Draw the static characteristics of S. C. R. and explain its different states of operation. Define Holding current and Latching current.	CO2	PO3	10
